

**OptiMOS<sup>™</sup>3 Power-Transistor**
**Features**

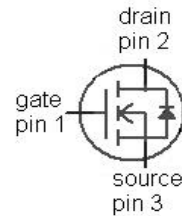
- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Halogen-free according to IEC61249-2-21

**Product Summary**

$V_{DS}$	80	V
$R_{DS(on),max}$	2.8	m $\Omega$
$I_D$	89	A



<b>Type</b>	IPA028N08N3 G
<b>Package</b>	PG-TO-220-FP
<b>Marking</b>	028N08N


**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}^{2)}$	89	A
		$T_C=100\text{ °C}$	62	
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	352	
Avalanche energy, single pulse <sup>4)</sup>	$E_{AS}$	$I_D=89\text{ A}, R_{GS}=25\ \Omega$	1430	mJ
Gate source voltage	$V_{GS}$		$\pm 20$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	42	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

<sup>1)</sup>J-STD20 and JESD22

<sup>2)</sup> Current is limited by package; with an  $R_{thJC}=0.5K/W$  in a standard TO-220 package the chip is able to carry 251A.

<sup>3)</sup> See figure 3 for more detailed information

<sup>4)</sup> See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics</b>						
Thermal resistance, junction - case	$R_{thJC}$		-	-	3.6	K/W
<b>Electrical characteristics, at <math>T_j=25\text{ °C}</math>, unless otherwise specified</b>						
<b>Static characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$	80	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=270\text{ }\mu\text{A}$	2	2.8	3.5	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$ , $I_D=89\text{ A}$	-	2.4	2.8	m $\Omega$
		$V_{GS}=6\text{ V}$ , $I_D=44\text{ A}$	-	2.8	4.2	
Gate resistance	$R_G$		-	2.7	-	$\Omega$
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=89\text{ A}$	89	178	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=40\text{ V},$ $f=1\text{ MHz}$	-	10700	14200	pF
Output capacitance	$C_{oss}$		-	2890	3840	
Reverse transfer capacitance	$C_{rss}$		-	100	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=40\text{ V}, V_{GS}=10\text{ V},$ $I_D=89\text{ A}, R_{G,ext}=1.6\ \Omega$	-	30	-	ns
Rise time	$t_r$		-	59	-	
Turn-off delay time	$t_{d(off)}$		-	77	-	
Fall time	$t_f$		-	26	-	

**Gate Charge Characteristics<sup>5)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=40\text{ V}, I_D=89\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	50	-	nC
Gate to drain charge	$Q_{gd}$		-	30	-	
Switching charge	$Q_{sw}$		-	50	-	
Gate charge total	$Q_g$		-	155	206	
Gate plateau voltage	$V_{plateau}$		-	4.6	-	
Output charge	$Q_{oss}$	$V_{DD}=40\text{ V}, V_{GS}=0\text{ V}$	-	210	279	nC

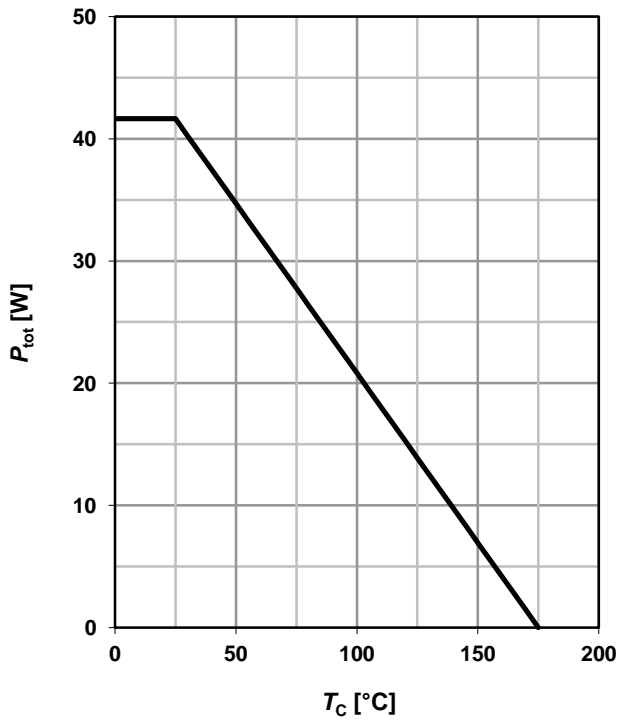
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	89	A
Diode pulse current	$I_{S,pulse}$		-	-	356	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=89\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.9	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=40\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	78	-	ns
Reverse recovery charge	$Q_{rr}$		-	181	-	nC

<sup>5)</sup> See figure 16 for gate charge parameter definition

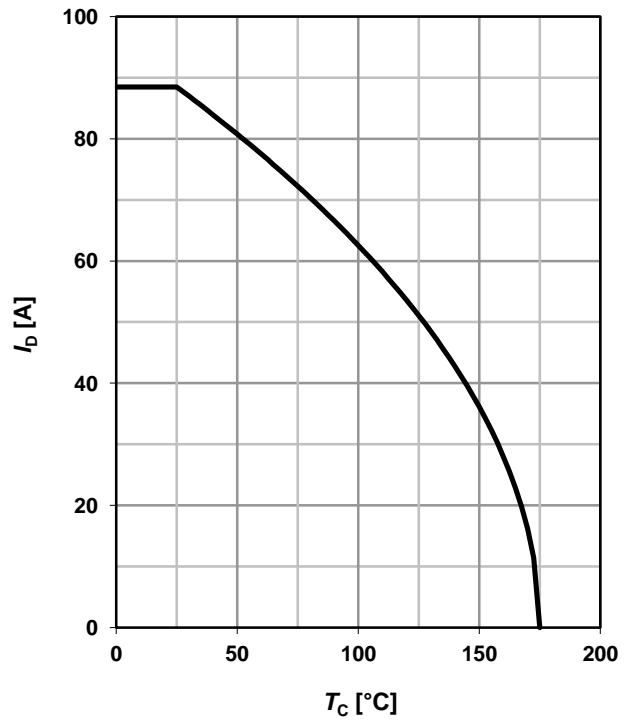
### 1 Power dissipation

$$P_{tot}=f(T_C)$$



### 2 Drain current

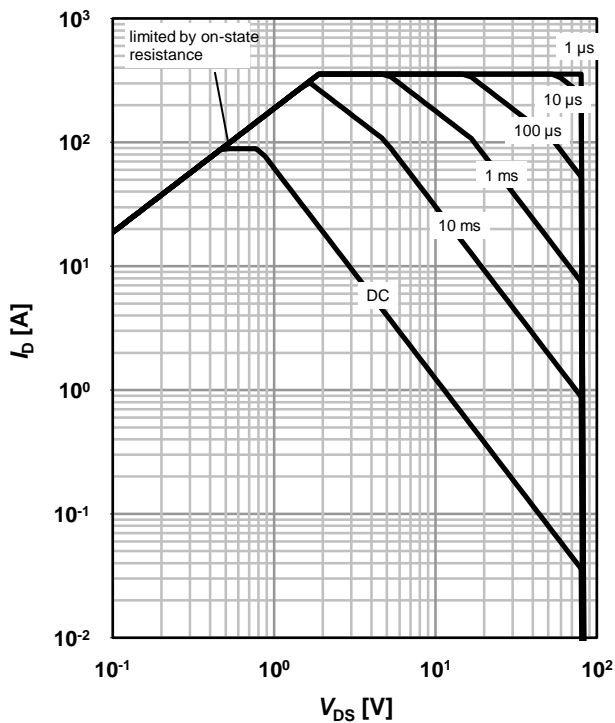
$$I_D=f(T_C); V_{GS} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D=f(V_{DS}); T_C=25 \text{ °C}; D=0$$

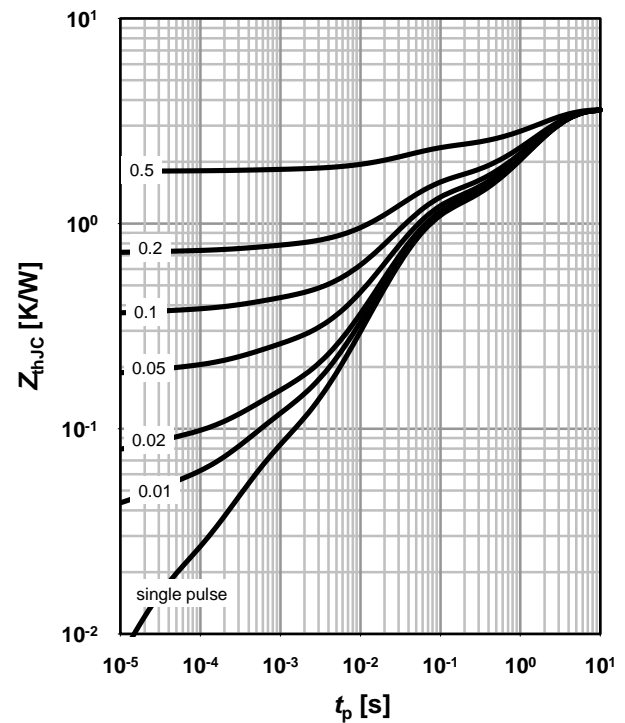
parameter:  $t_p$



### 4 Max. transient thermal impedance

$$Z_{thJC}=f(t_p)$$

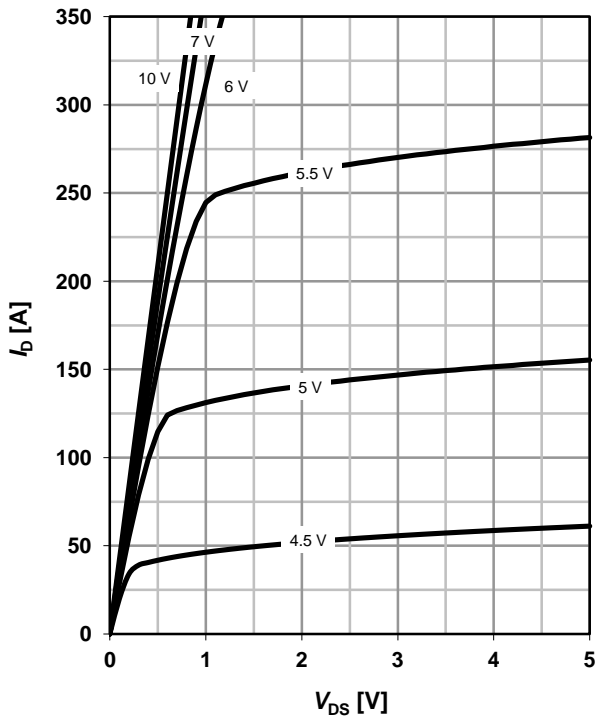
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

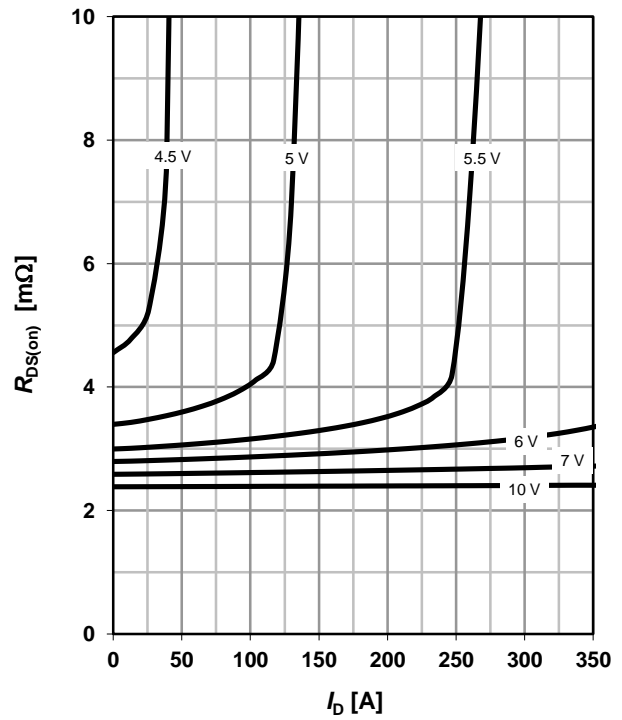
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

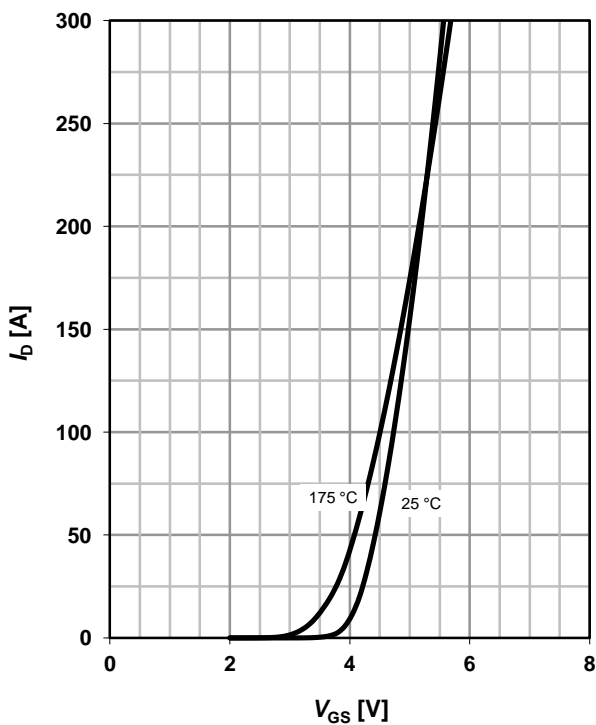
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

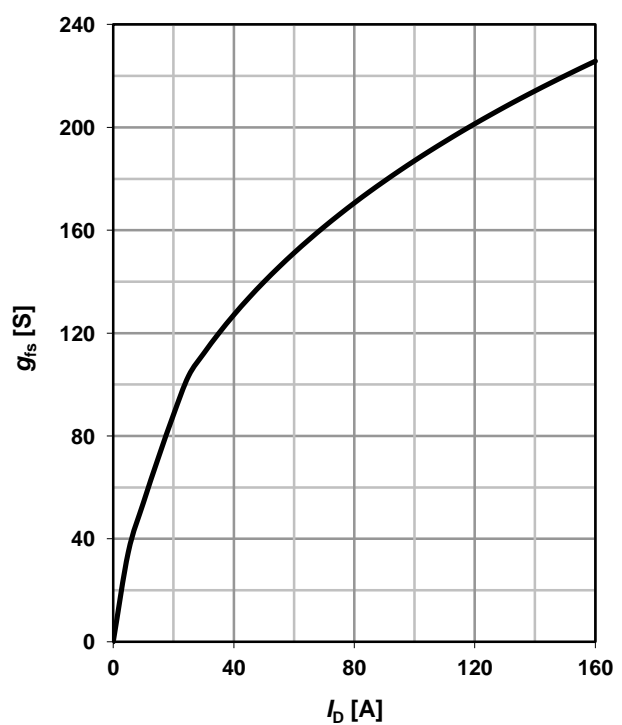
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



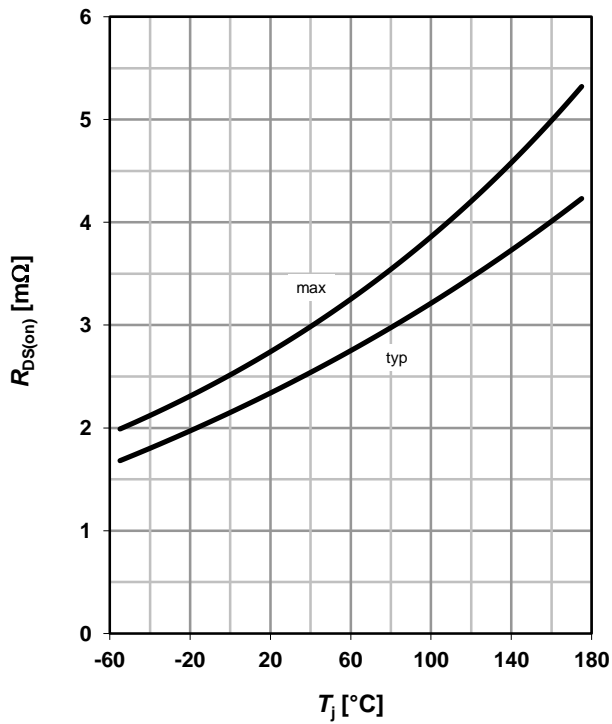
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



**9 Drain-source on-state resistance**

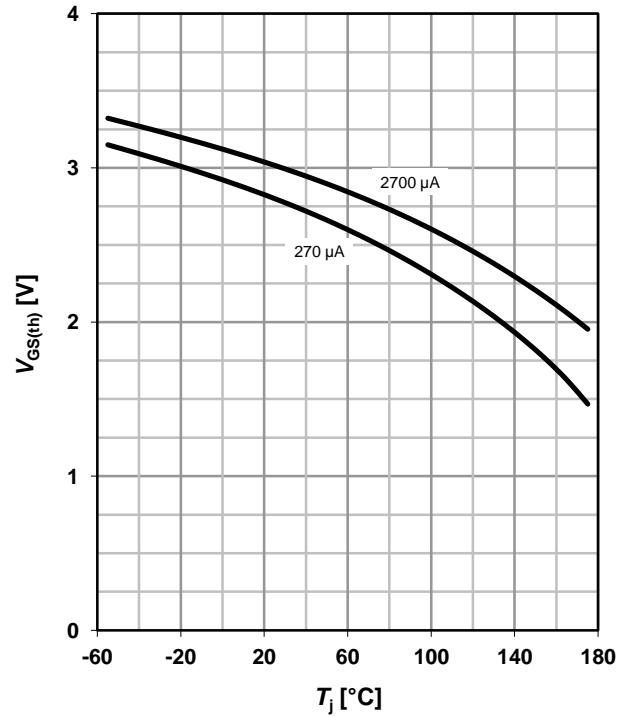
$R_{DS(on)}=f(T_j)$ ;  $I_D=89\text{ A}$ ;  $V_{GS}=10\text{ V}$



**10 Typ. gate threshold voltage**

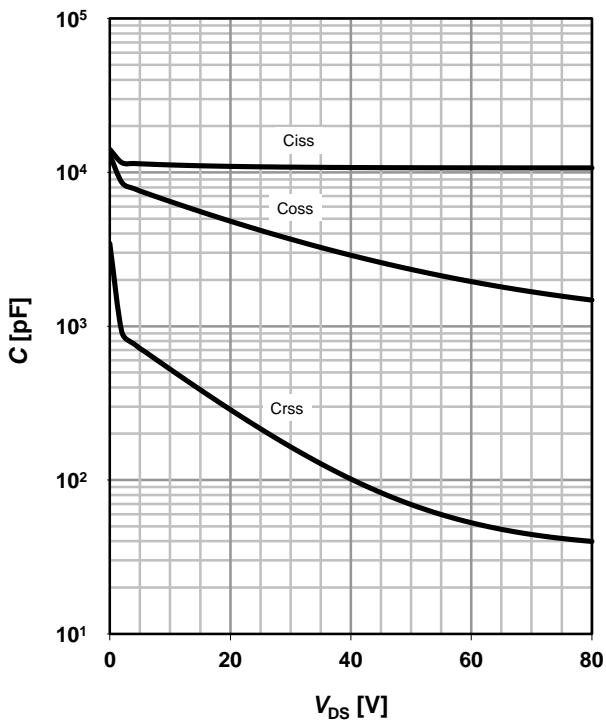
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

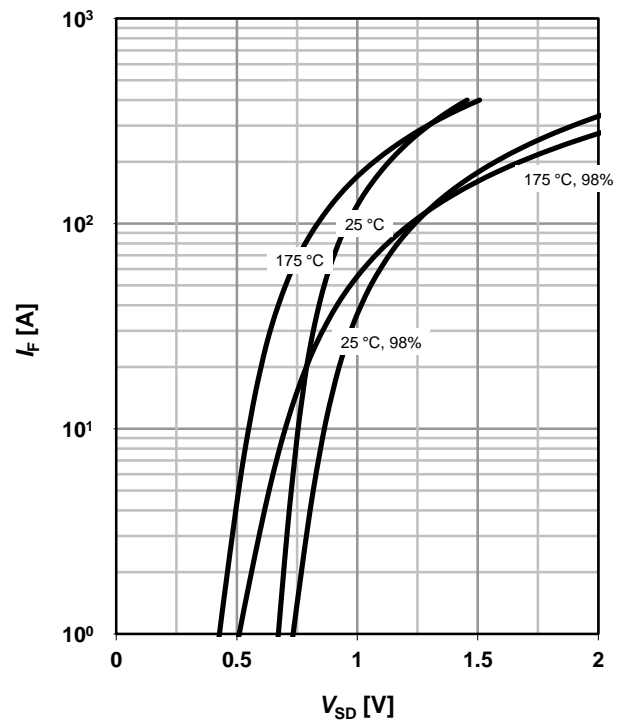
$C=f(V_{DS})$ ;  $V_{GS}=0\text{ V}$ ;  $f=1\text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

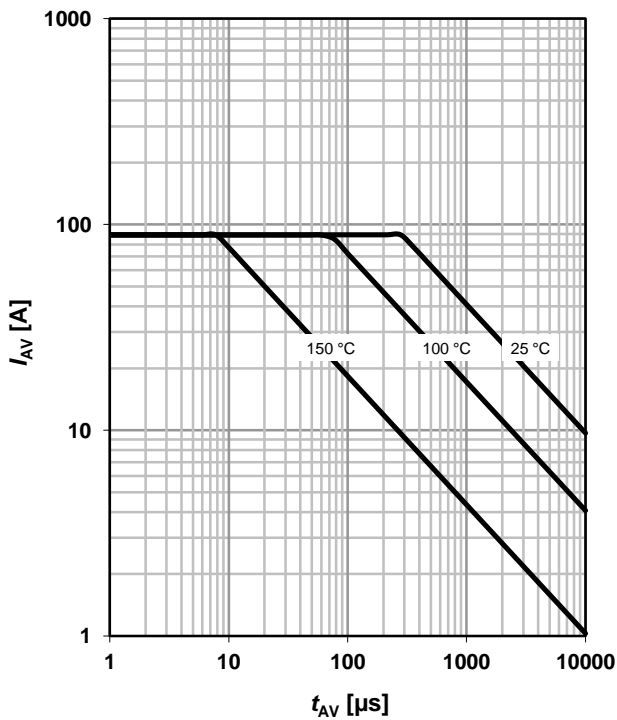
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

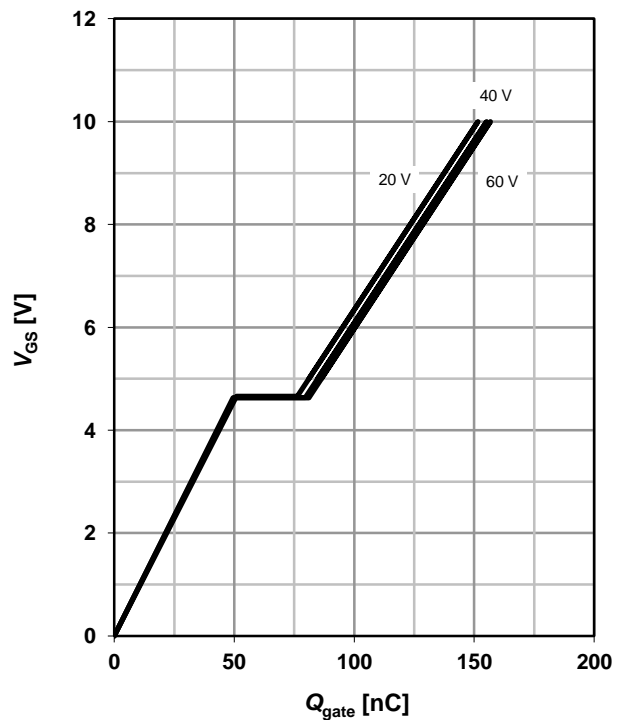
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

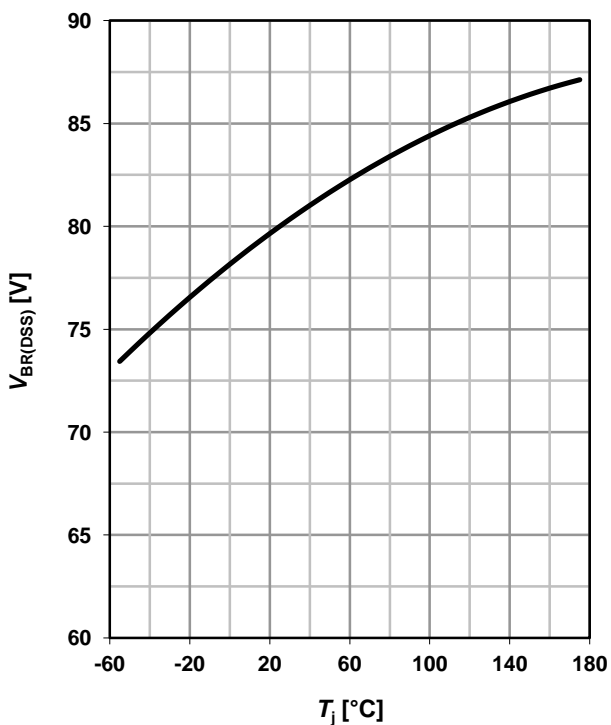
$V_{GS}=f(Q_{\text{gate}}); I_D=89\text{A pulsed}$

parameter:  $V_{DD}$

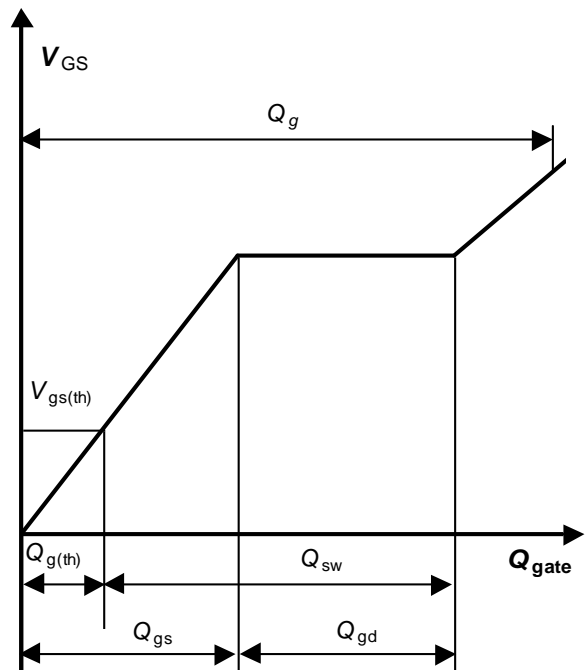


**15 Drain-source breakdown voltage**

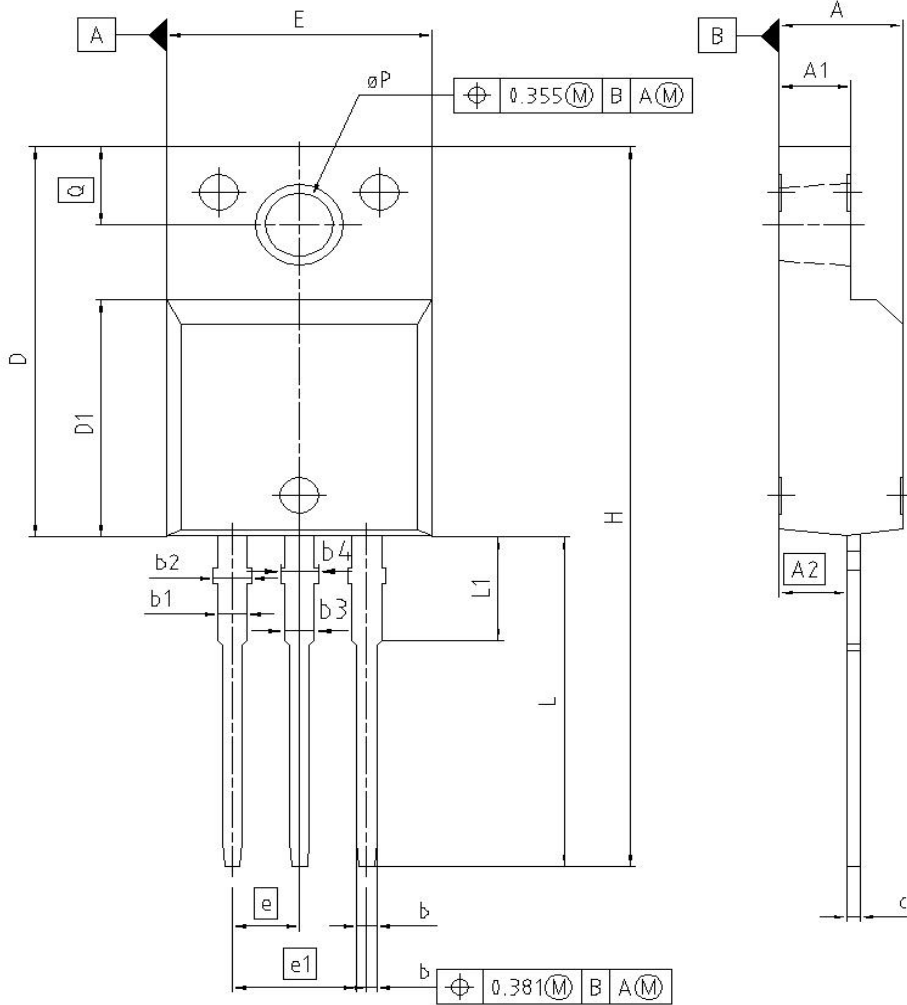
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



**16 Gate charge waveforms**



PG-TO-220-FP



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

REFERENCE  
./...

SCALE  
0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE  
08-01-2007

FILE  
TO220\_2



**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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